

Part Number

Customer

Category	Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm
	2.0	Primary Flat Orientation	{110} +/- 1 degree
	3.0	Primary Flat Length	32.50 +/- 2.50 mm
	4.0	Secondary Flat Orientation	none
	5.0	Secondary Flat Length	none
	6.0	Overall Thickness	333.00 +/- 11.00 µm
	7.0	Total Thickness Variation (TTV)	<5.00µm
	8.0	Bow	<100.00µm
	9.0	Warp	<100.00µm
	10.0	Edge Chips	0
	11.0	Edge Exclusion	5mm
HandleSilicon	12.0	Handle Growth Method	CZ
	13.0	Handle Orientation	{100} +/- 0.5 degree
	14.0	Handle Thickness	300.00 +/- 10.00 µm
	15.0	Handle Doping Type	N
	16.0	Handle Dopant	Phos
	17.0	Handle Resistivity	0.001 - 0.0015 Ohm-cm
	18.0	Backside Finish	Polished with oxide lasermark and light handling marks
BuriedOxide	19.0	Oxide Type	Thermal
	20.0	Oxide Thickness	40,000.00 +/- 2,000.00 Å
	21.0	Oxide formed on	Handle and / or device Wafer
DeviceSilicon	22.0	Device Growth Method	CZ
	23.0	Device Orientation	{100} +/- 0.5 degree
	24.0	Nominal Thickness	30.00 +/- 1.00 µm
	25.0	Distance to device silicon edge from wafer edge	<= 2mm
	26.0	Device Doping Type	N
	27.0	Device Dopant	Phos
	28.0	Device Resistivity	0.001 - 0.0015 Ohm-cm
	29.0	Voids	none
	30.0	Haze	none
	31.0	LPD Count	<30 @0.3µm

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Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		
	2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.		
	3. 9 point measurement are as shown in the diagram below:		



Additional Information